

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07690 D 7-33-65

SILICON NPN TRIPLE DIFFUSED TYPE

2SC3309

SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS.

HIGH SPEED DC-DC CONVERTER APPLICATION.

FEATURES:

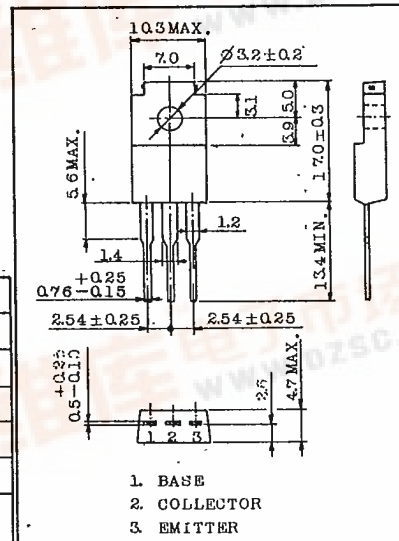
- Excellent Switching Times
 $t_r=1.0\mu s(\text{Max.}), t_f=1.0\mu s(\text{Max.})$ at $I_C=0.8A$
- High Collector Breakdown Voltage: $V_{CE0}=400V$

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	500	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	2	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	$T_a=25^\circ C$	2.0
		$T_c=25^\circ C$	20
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$

INDUSTRIAL APPLICATIONS

Unit in mm



J E D B C	-
E I A J	-
TOSHIBA	2-10 L1 A

Weight : 2.1g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=400V, I_E=0$	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$	-	-	1	mA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	500	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	400	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=0.1A$	20	-	-	
		$V_{CE}=5V, I_C=1A$	8	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=0.2A$	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=0.2A$	-	-	1.5	V
Switching Time	Rise Time	t_r	-	-	1.0	μs
	Storage Time	t_{stg}	-	-	2.5	
	Fall Time	t_f	-	-	1.0	

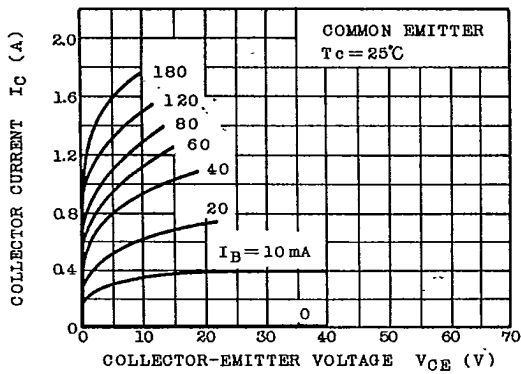


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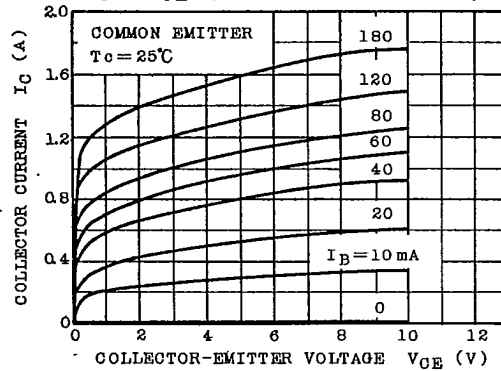
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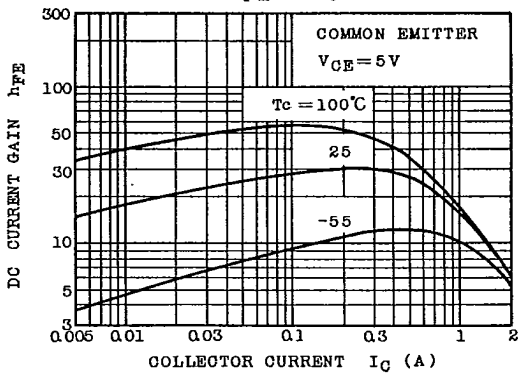
STATIC CHARACTERISTICS



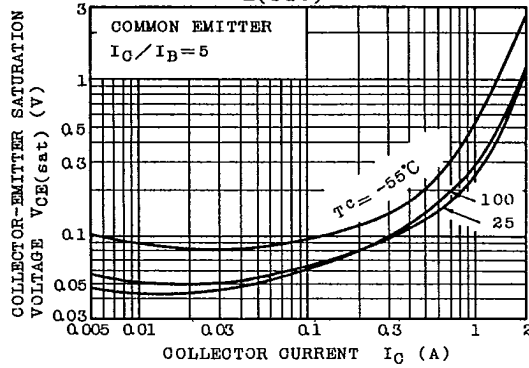
IC - VCE (LOW VOLTAGE REGION)



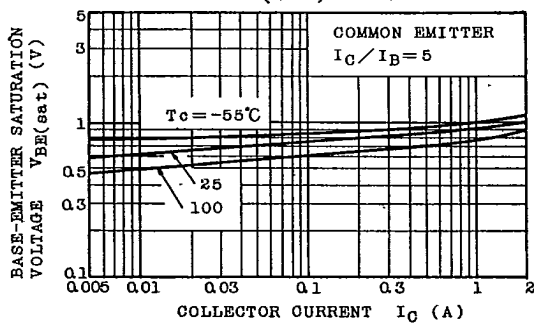
hFE - IC



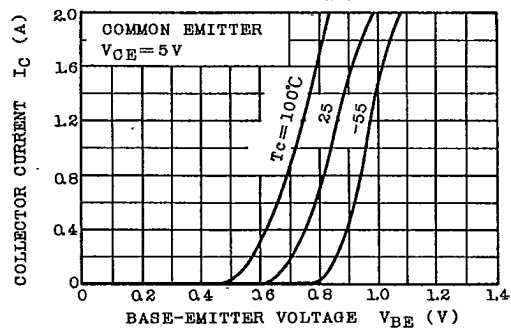
VCE(sat) - IC



VBE(sat) - IC



IC - VBE



TOSHIBA CORPORATION

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